Schottky barrier diode

RB495D

●Applications

Low current rectification

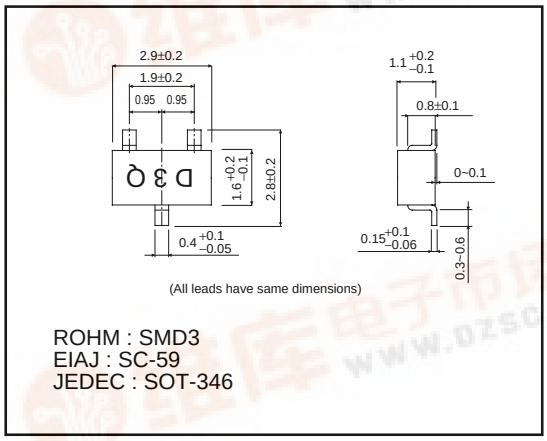
●Features

1) Small surface mounting type. (SMD3)
2) Two diodes with common cathode for excellent installation efficiency.
3) High reliability.

●Construction

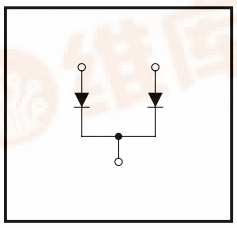
Silicon epitaxial planar

●External dimensions (Units : mm)



ROHM : SMD3
EIAJ : SC-59
JEDEC : SOT-346

●Circuit



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltege	V_R	25	V
Mean rectifying current*1	I_O	0.4	A
Peak forward surge current*2	I_{FSM}	2	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−40~+125	°C
Operating temperture	Topr	−30~+85	°C

∗1 Mean output current per element : Io / 2
∗2 60Hz for 1 ∿

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	–	–	0.30	V	I_F=10mA
	V_{F2}	–	–	0.50	V	I_F=200mA
Reverse current	I_R	–	–	70	μA	V_R=25V

Note) ESD sensiteve product handling required.

●**Electrical characteristic curves** (Ta = 25°C)

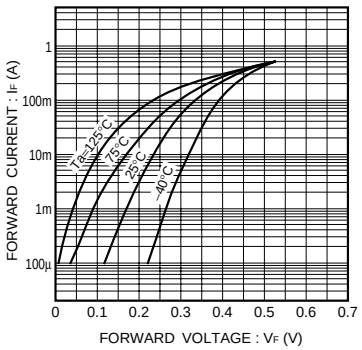


Fig.1 Forward characteristics

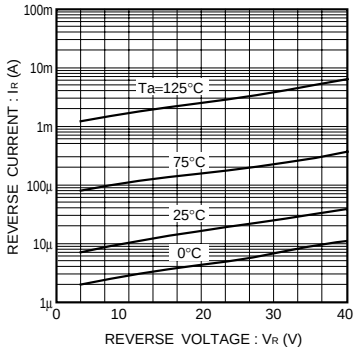


Fig.2 Reverse characteristics

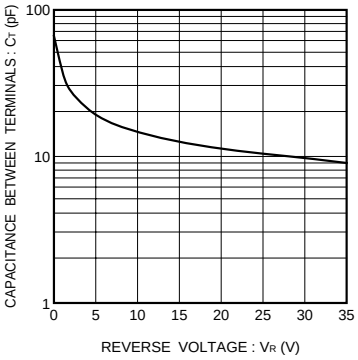


Fig.3 Capacitance between terminals characteristics